

Influence of thickness and surface composition on the stability of ferroelectric polarization in HfO₂

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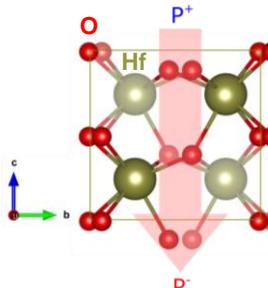
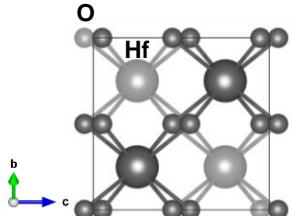
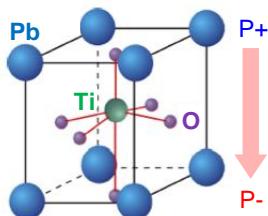
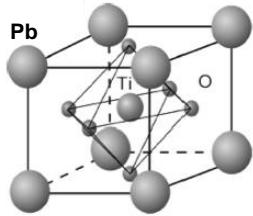
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Structural Origin of Ferroelectricity

Comparing perovskites to fluorite ferroelectrics

Examples



parent
nonpolar phase

polar phase

Oxygen
octahedron
in perovskites

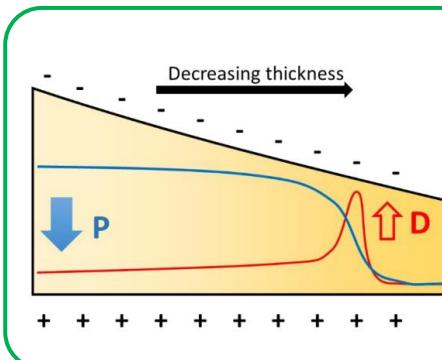
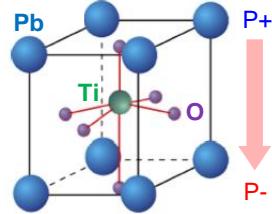
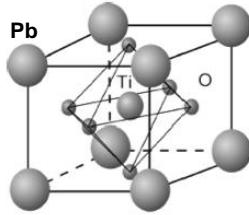
Oxygen
hexahedron
in fluorites

HfO₂: a superior ferroelectric for nanoscale applications

Conventional Perovskite Ferroelectrics

Material	Pb(Zr, Ti)O ₃	SrBi ₂ Ta ₂ O ₉	BiFeO ₃	HfO ₂ -based
P _r ($\mu\text{C}/\text{cm}^2$)	10-40	5-10	90-95	10-40
E _c (kV/cm)	50-70	30-50	100-1500	2000-5000
ϵ_0	~400	~200	~50	~25
Minimum film thickness (nm)	>50	>25	>10	~1
CMOS compatibility?	No	No	No	Yes

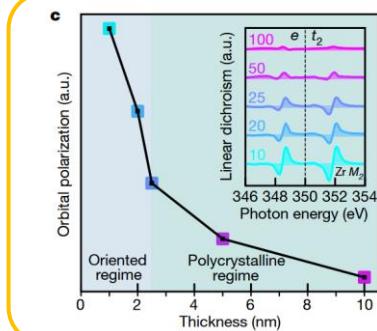
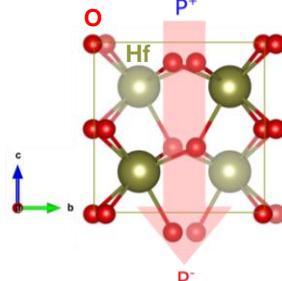
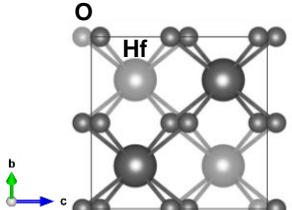
PbTiO₃



Ferroelectricity is generally unstable at small thickness for perovskites

[1]

HfO₂



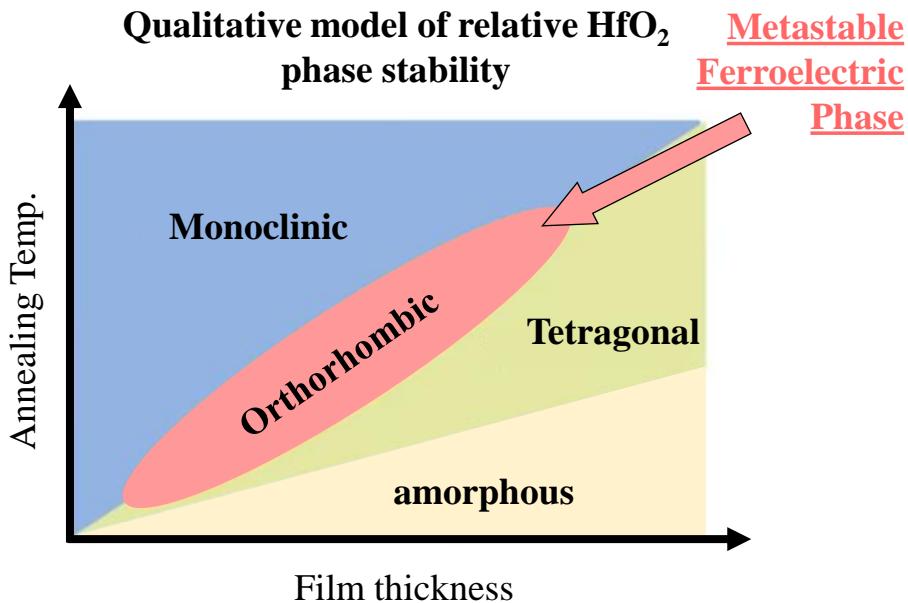
Enhanced polarization in FE-HfO₂ at the nanoscale

[2]

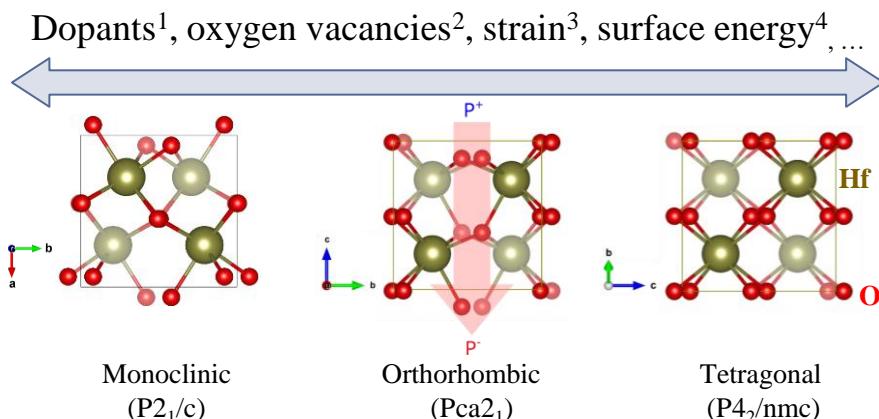
[1] Östling, Mikael, et al. *Thin solid films* 469 (2004): 444-449.

[2] Cheema, Suraj S., et al. *Nature* 580.7804 (2020): 478-482.

Challenges with integrating ferroelectric HfO_2



- Generally nonpolar monoclinic phase needs to be kinetically suppressed during crystallization



- Many other factors can contribute to stability of polar orthorhombic phase

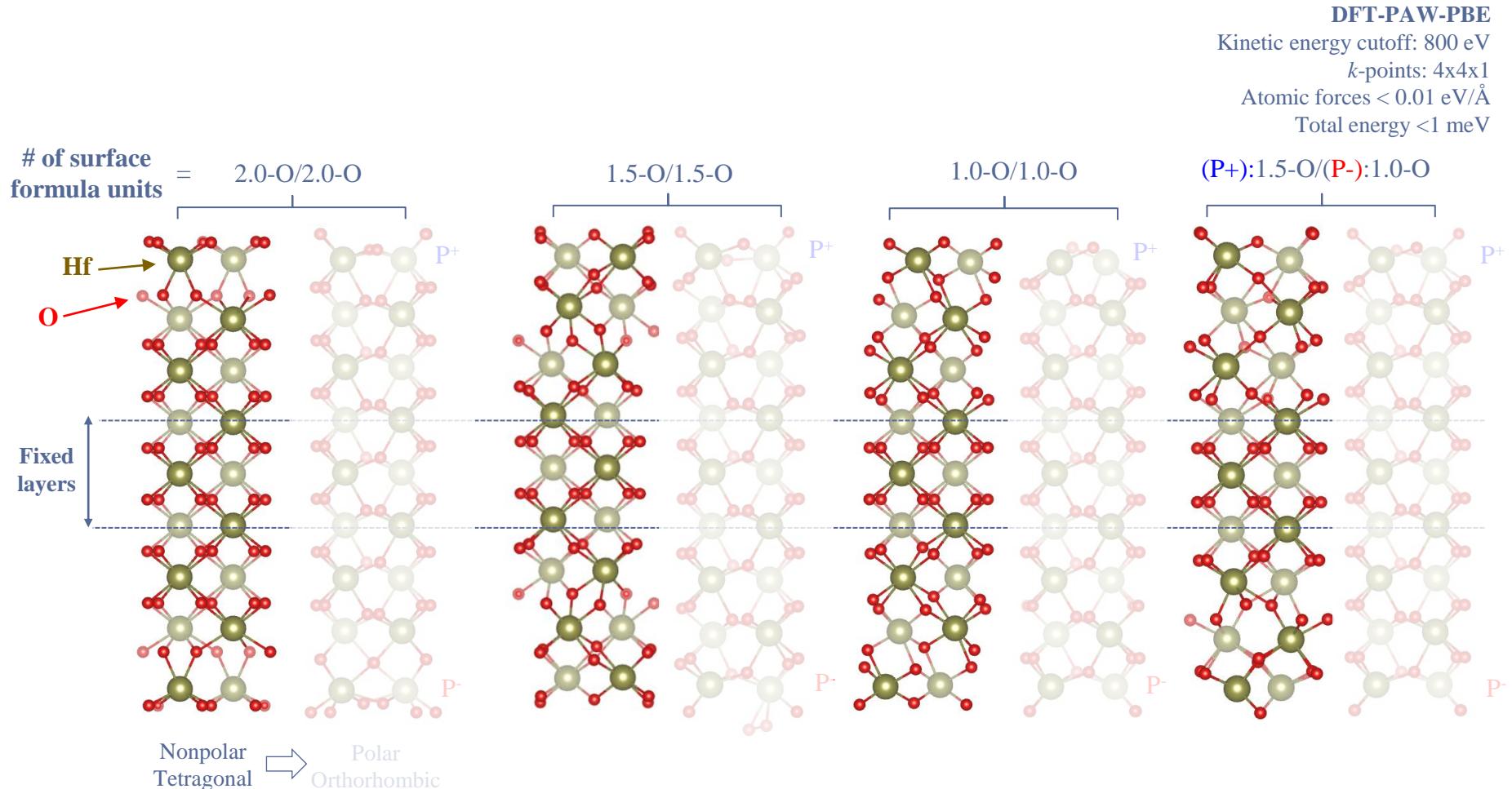
[1] Batra, Rohit, et al. *Chem. Mater.* 29.21 (2017): 9102-9109;

[2] Zhou, Y., et al. *Comput. Mater. Sci.* 167 (2019): 143-150.

[3] Batra, Rohit, et al. *J. Phys. Chem* 121.8 (2017): 4139-4145;

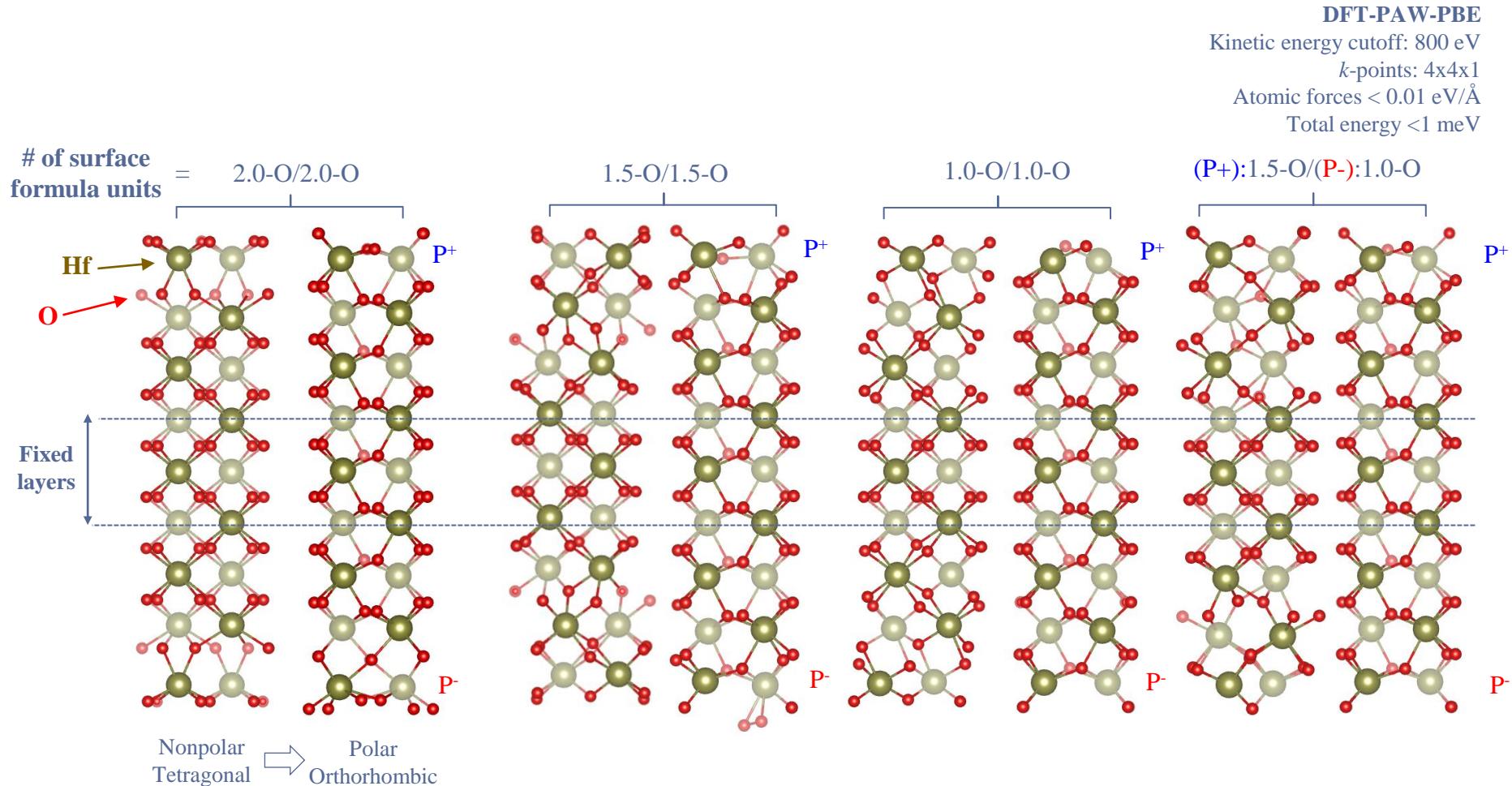
[4] Batra, Rohit, Huan Doan Tran, and Rampi Ramprasad. *Appl. Phys. Lett.* 108.17 (2016): 172902

How does ferroelectric polarization influence surface stability?



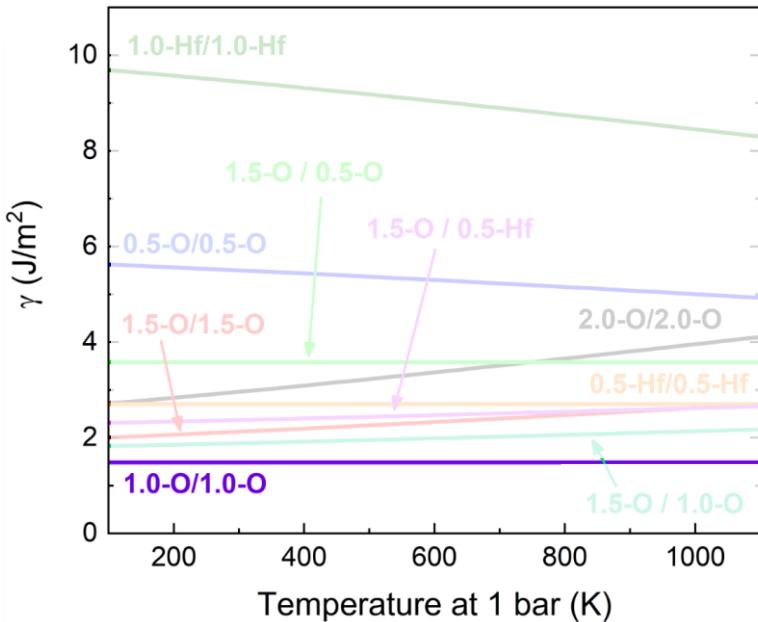
It is necessary to decouple the influence of surface composition & ferroelectric polarization on the surface stability

How does ferroelectric polarization influence surface stability?



It is necessary to decouple the influence of surface composition & ferroelectric polarization on the surface stability

Surface Energy of Nonpolar Tetragonal HfO₂



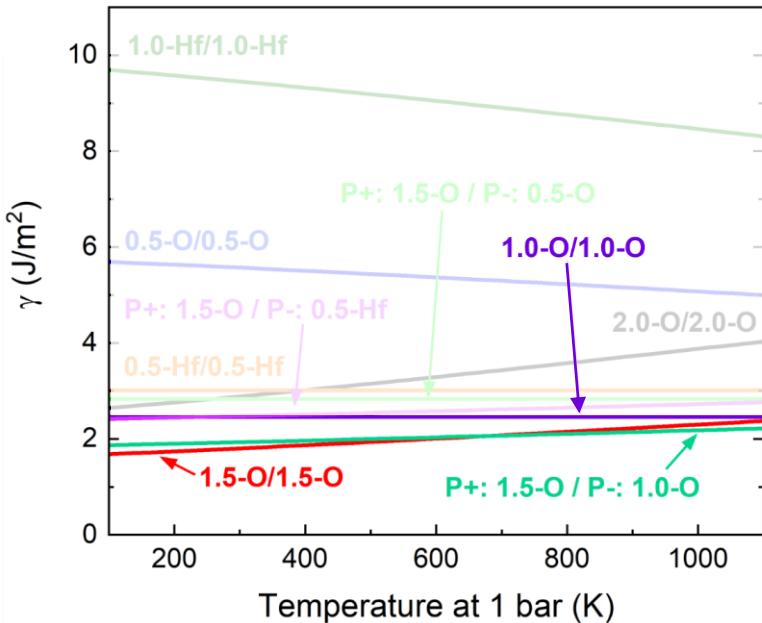
Calculating average surface free energy:

$$\gamma_{avg} = \frac{1}{2A} \begin{pmatrix} G_{slab}(T, P, N_{Hf}, N_O) \\ -N_{Hf}g_{HfO_2}^{bulk}(T, P) \\ +(2N_{Hf} - N_O)\mu_O(T, P) \end{pmatrix}$$

$$\mu_O(T, p) = \mu_O(T, p^\circ) + \frac{1}{2} kT \ln\left(\frac{p}{p^\circ}\right)$$

Most thermodynamically stable surface composition for a nonpolar slab is 1.0-O/1.0-O, which corresponds to a stoichiometric slab

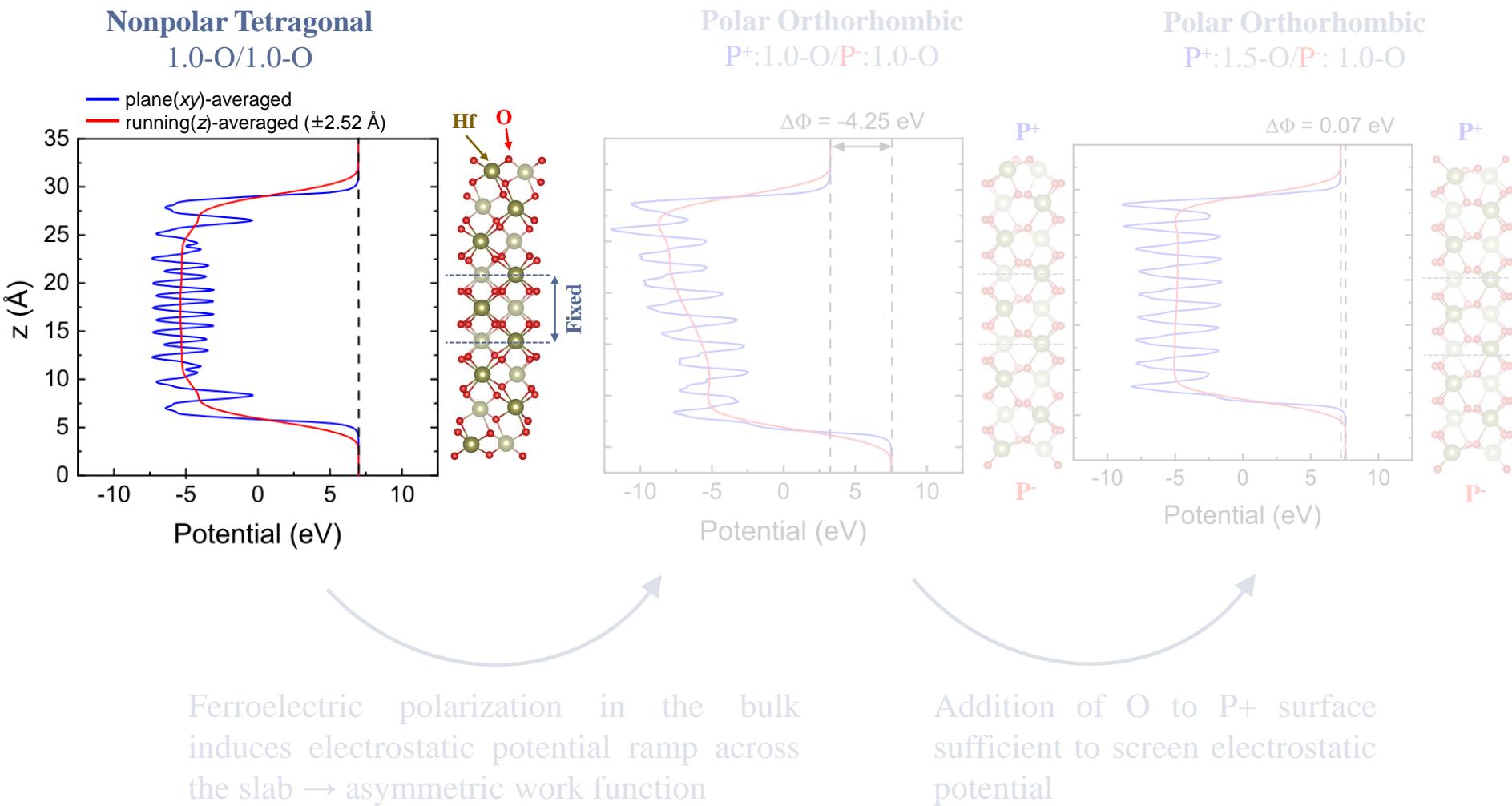
Surface Energy of Polar Orthorhombic HfO_2



The **1.0-O/1.0-O** surface composition is destabilized when ferroelectric polarization is introduced

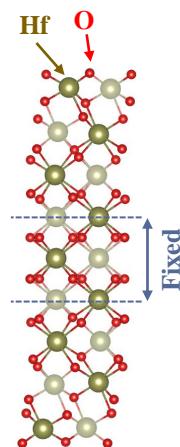
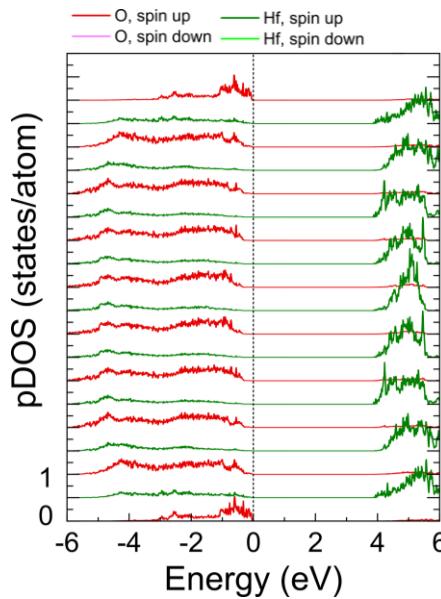
Most thermodynamically stable surface composition for a polar slab at high temperature is **P+:1.5-O/P-:1.0-O**

Electrostatic potential profiles provide insights into surface stability

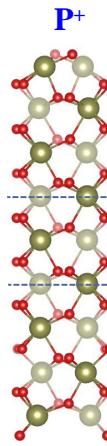
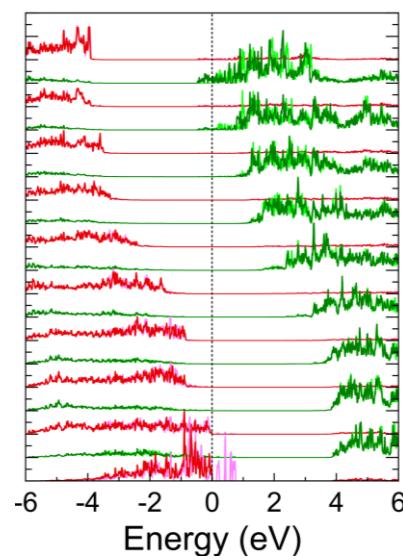


Ionic screening of electrostatic potential alleviates band bending

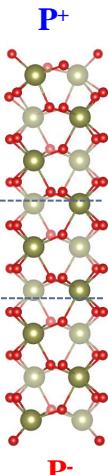
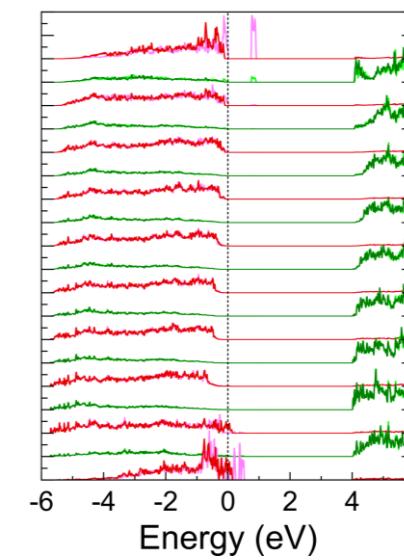
Nonpolar Tetragonal
1.0-O/1.0-O



Polar Orthorhombic
 $P^+:1.0\text{-O}/P^-:1.0\text{-O}$



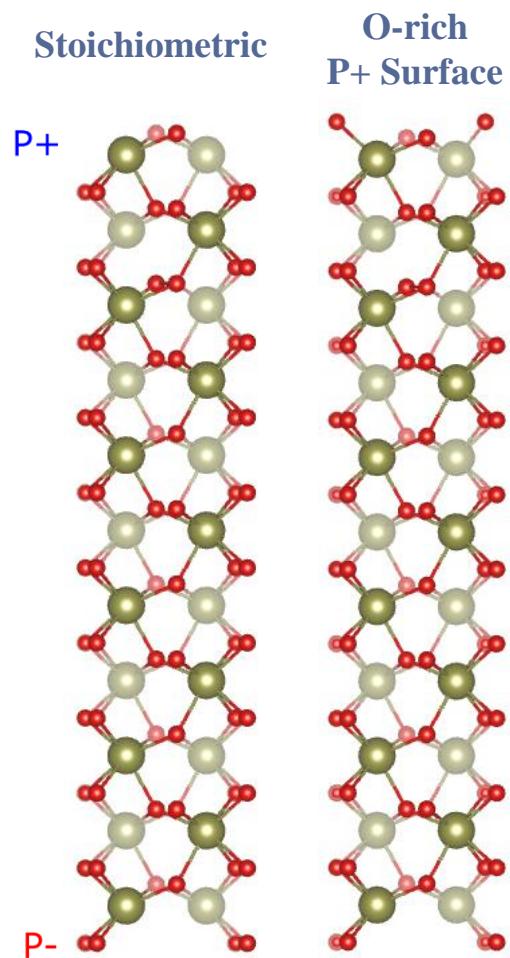
Polar Orthorhombic
 $P^+:1.5\text{-O}/P^-:1.0\text{-O}$



Surface metallization after dielectric breakdown due to electrostatic potential

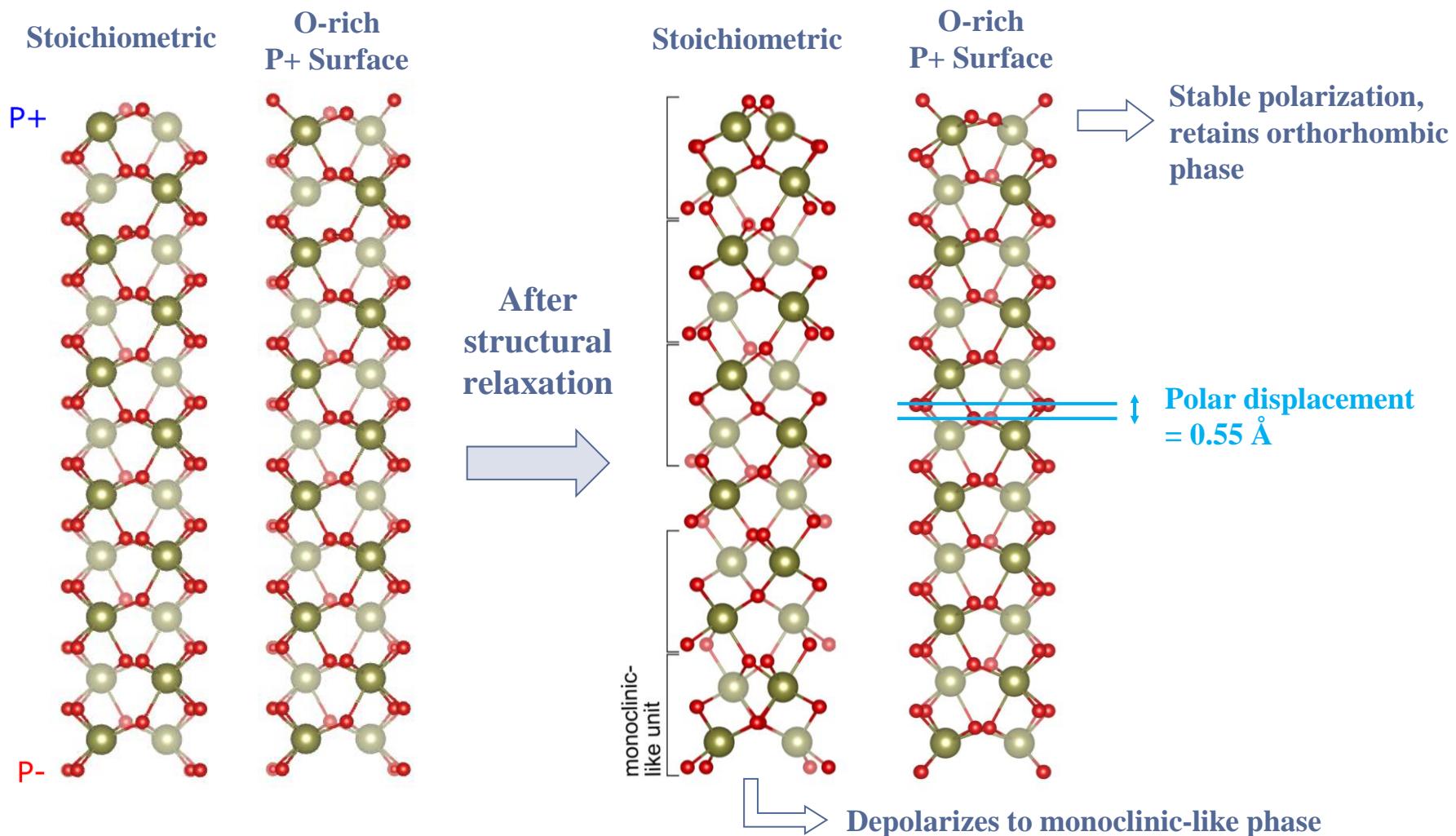
Charge compensation from additional O on P⁺ surface screens electrostatic potential to avoid dielectric breakdown

Effect of Surf. Comp. on HfO_2 Ferroelectric Stability



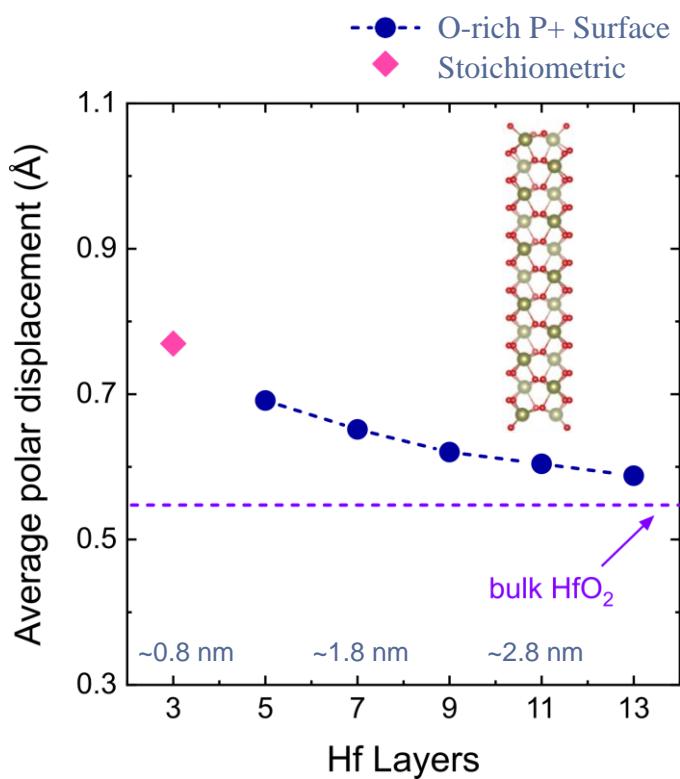
How does the surface composition influence the ferroelectric stability of HfO_2 ?

Effect of Surf. Comp. on HfO_2 Ferroelectric Stability

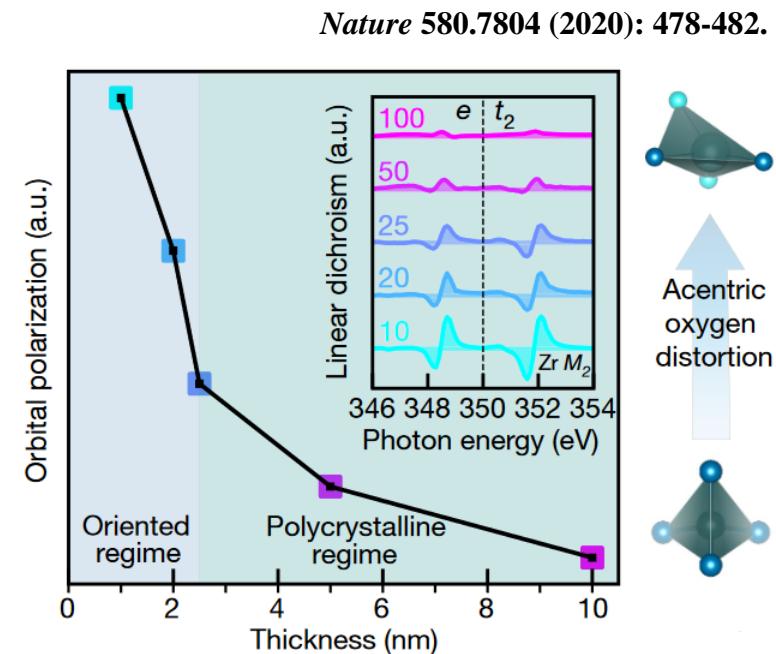


Controlling surface composition can be used to stabilize ferroelectricity in HfO_2

Effect of thickness on polarization of HfO_2



Enhanced ferroelectricity in ultrathin films grown directly on silicon



1. No size limit to ferroelectric stability
2. Increased polarization with decreasing thickness
 - Large band gap enables stable, increasing polarization at small thicknesses

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